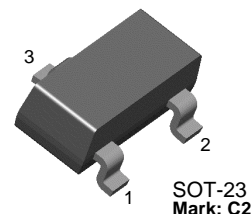


# BCW30

BCW30

## PNP General Purpose Amplifier

- This device is designed for general purpose medium power amplifiers and switches requiring collector currents to 300mA.
- Sourced from process 68.



1. Base 2. Emitter 3. Collector

## Absolute Maximum Ratings \* $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CEO}$	Collector-Emitter Voltage	-32	V
$V_{CES}$	Collector-Emitter Voltage	-32	V
$V_{EBO}$	Emitter-Base Voltage	-5.0	V
$I_C$	Collector current - Continuous	-500	mA
$T_J, T_{stg}$	Junction and Storage Temperature	-55 ~ +150	$^{\circ}\text{C}$

\* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

### NOTES:

- These ratings are based on a maximum junction temperature of 150 degrees C.
- These are state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

## Electrical Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

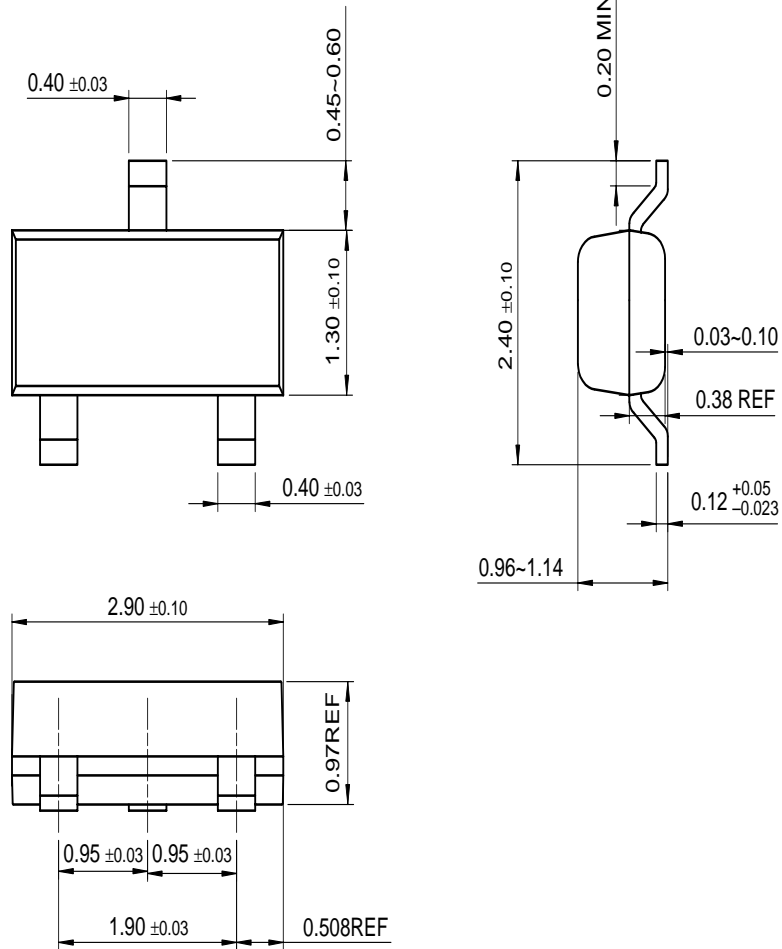
Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
<b>Off Characteristics</b>						
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = -10\mu\text{A}, I_E = 0$	-32			V
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -2.0\text{mA}, I_B = 0$	-32			V
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage	$I_C = -10\mu\text{A}, I_E = 0$	-32			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_C = -10\mu\text{A}, I_C = 0$	-5.0			V
$I_{CBO}$	Collector Cutoff Current	$V_{CB} = -32\text{V}, I_E = 0$ $V_{CB} = -32\text{V}, I_E = 0, T_A = +100^{\circ}\text{C}$			-100 -10	nA $\mu\text{A}$
<b>On Characteristics</b>						
$h_{FE}$	DC Current Gain	$V_{CE} = -5.0\text{V}, I_C = -2.0\text{mA}$	215		500	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -10\text{mA}, I_B = -0.5\text{mA}$			-0.3	V
$V_{BE(on)}$	Base-Emitter On Voltage	$V_{CE} = -5.0\text{V}, I_C = -2.0\text{mA}$	-0.6		-0.7	V
<b>Small Signal Characteristics</b>						
NF	Noise Figure	$V_{CE} = -5.0\text{V}, I_C = -200\mu\text{A}$ $R_S = 2.0\text{k}\Omega, f = 1.0\text{kHz}$ $B_W = 200\text{Hz}$			10	dB

## Thermal Characteristics $T_A=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Max.	Units
$P_D$	Total Device Dissipation Derate above $25^{\circ}\text{C}$	350 2.8	mW $\text{mW}/^{\circ}\text{C}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	$^{\circ}\text{C}/\text{W}$

# Package Dimensions

## SOT-23



Dimensions in Millimeters

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